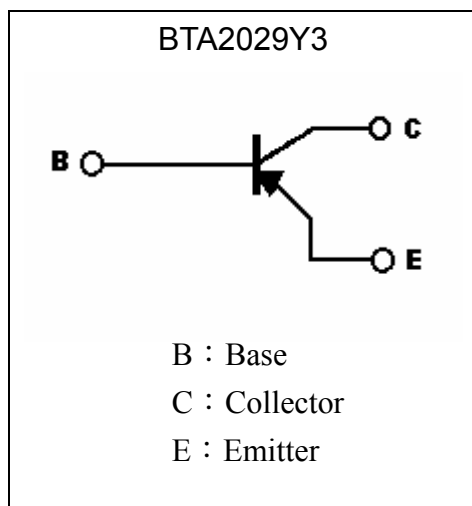
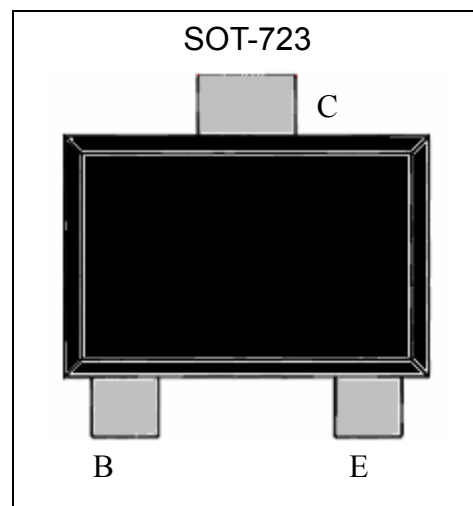


**General Purpose PNP Epitaxial Planar Transistor**

# BTA2029Y3

**Description**

- The BTA2029Y3 is designed for use in driver stage of AF amplifier and general purpose amplification.
- High  $H_{FE}$  and excellent linearity
- Complementary to BTC5658Y3.
- Pb-free package

**Symbol**

**Outline**

**Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CBO}$	-60	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Collector Current	$I_C$	-150	mA
Power Dissipation	$P_d$	150	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	833.3	°C/W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~+150	°C

**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-60	-	-	V	IC=-50μA
BVCEO	-50	-	-	V	IC=-1mA
BVEBO	-6	-	-	V	IE=-50μA
ICBO	-	-	-0.1	μA	VCB=-60V
IEBO	-	-	-0.1	μA	VEB=-6V
*VCE(sat)	-	-	-0.5	V	IC=-50mA, IB=-5mA
hFE	180	-	560	-	VCE=-6V, IC=-1mA
fT	-	140	-	MHz	VCE=-12V, IC=-2mA, f=30MHz
Cob	-	4	5	pF	VCB=-12V, IE=0, f=1MHz

\*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

**Marking Code and Classification of hFE**

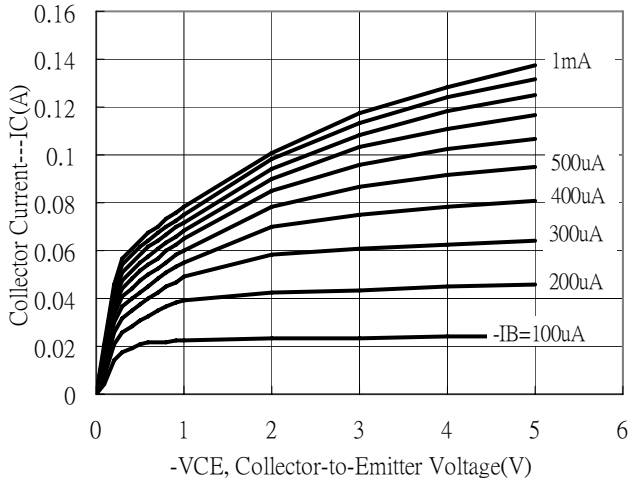
Rank	R	S
hFE Range	180-390	270-560
Marking	FR	FS

**Ordering Information**

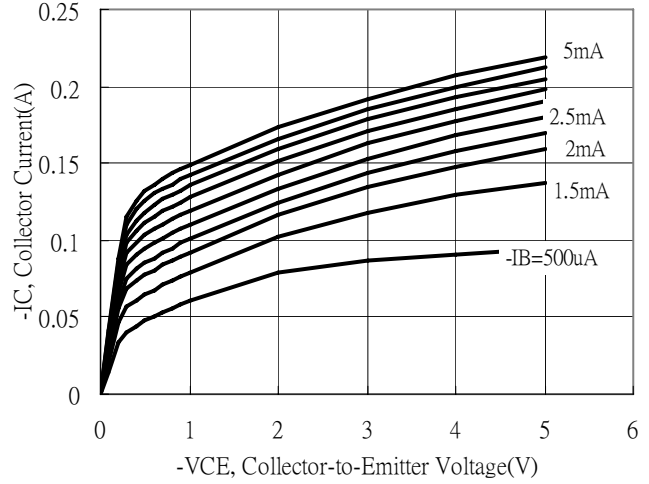
Device	Package	Shipping
BTA2029Y3	SOT-723 (Pb-free)	8000 pcs / Tape & Reel

**Typical Characteristics**

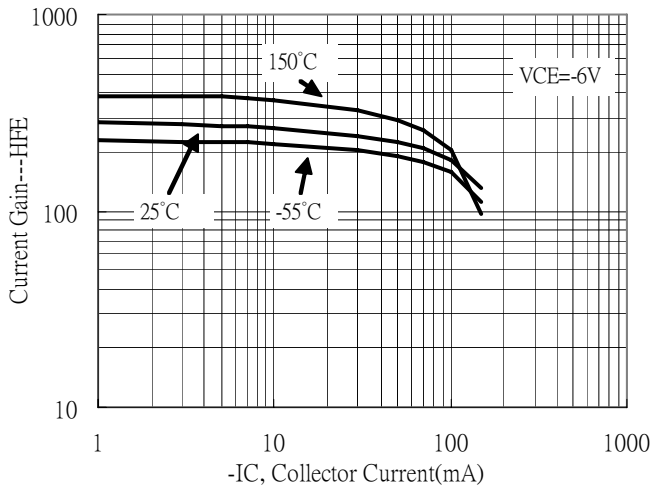
Emitter Grounded Output Characteristics



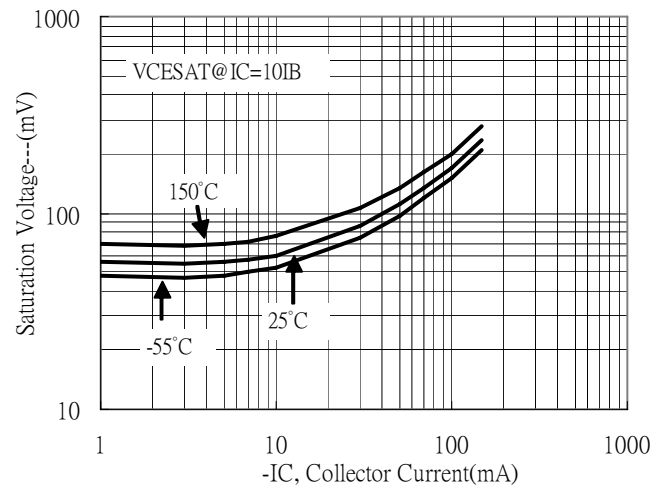
Emitter Grounded Output Characteristics



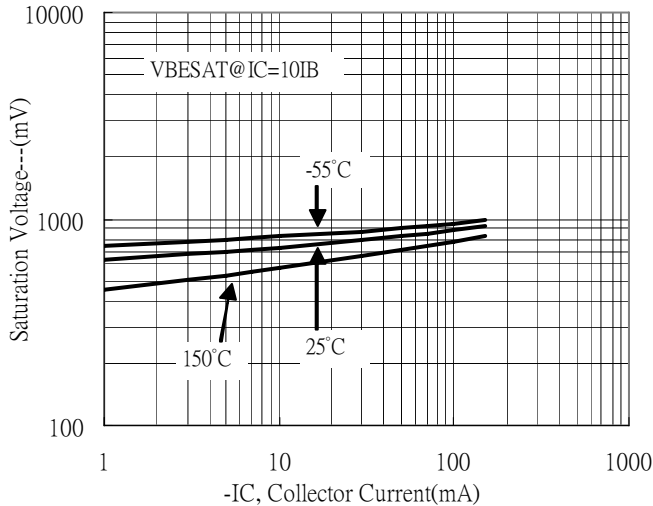
Current Gain vs Collector Current



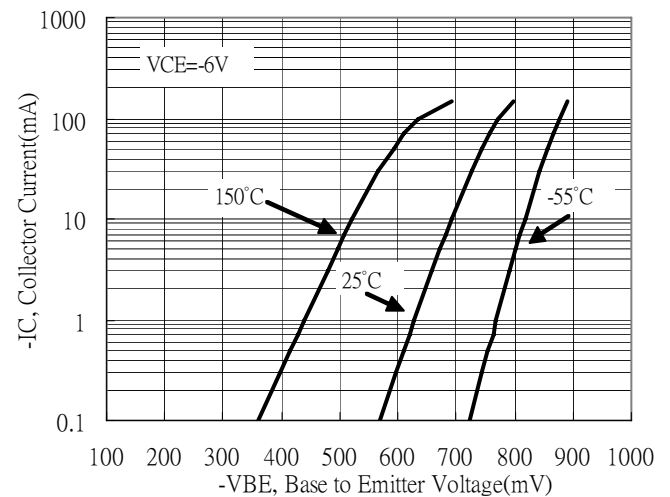
Saturation Voltage vs Collector Current



Saturation Voltage vs Collector Current

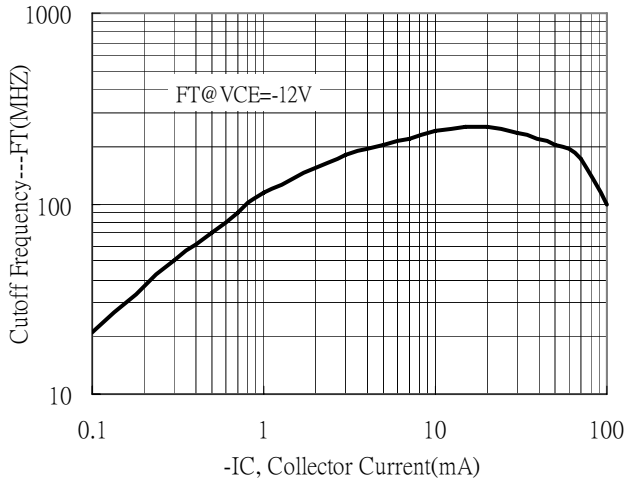


On Voltage vs Collector Current

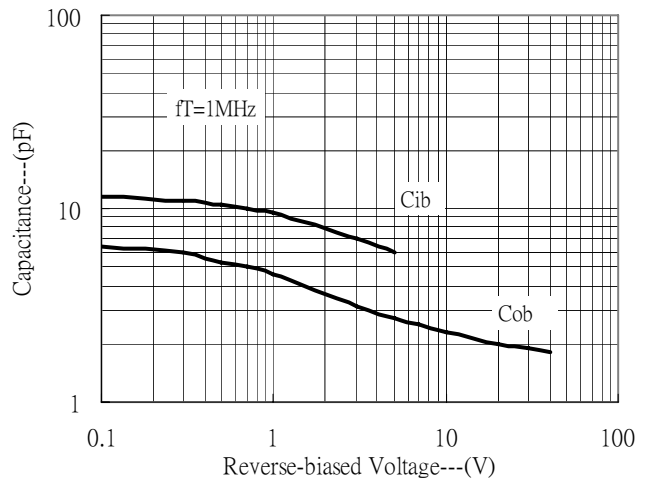


## Typical Characteristics

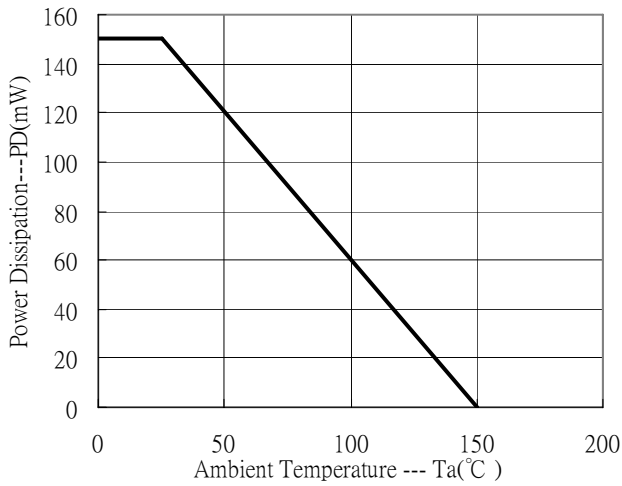
Cutoff Frequency vs Collector Current



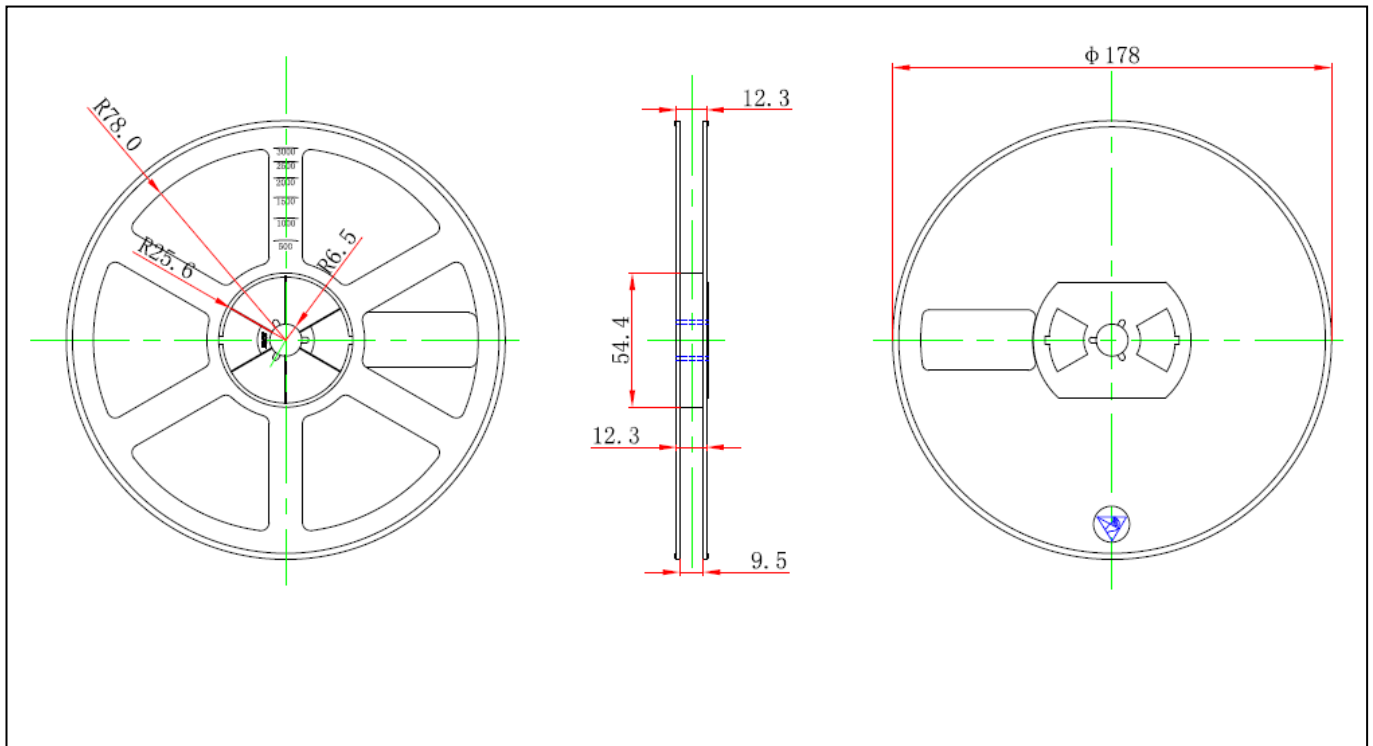
Capacitance Characteristics



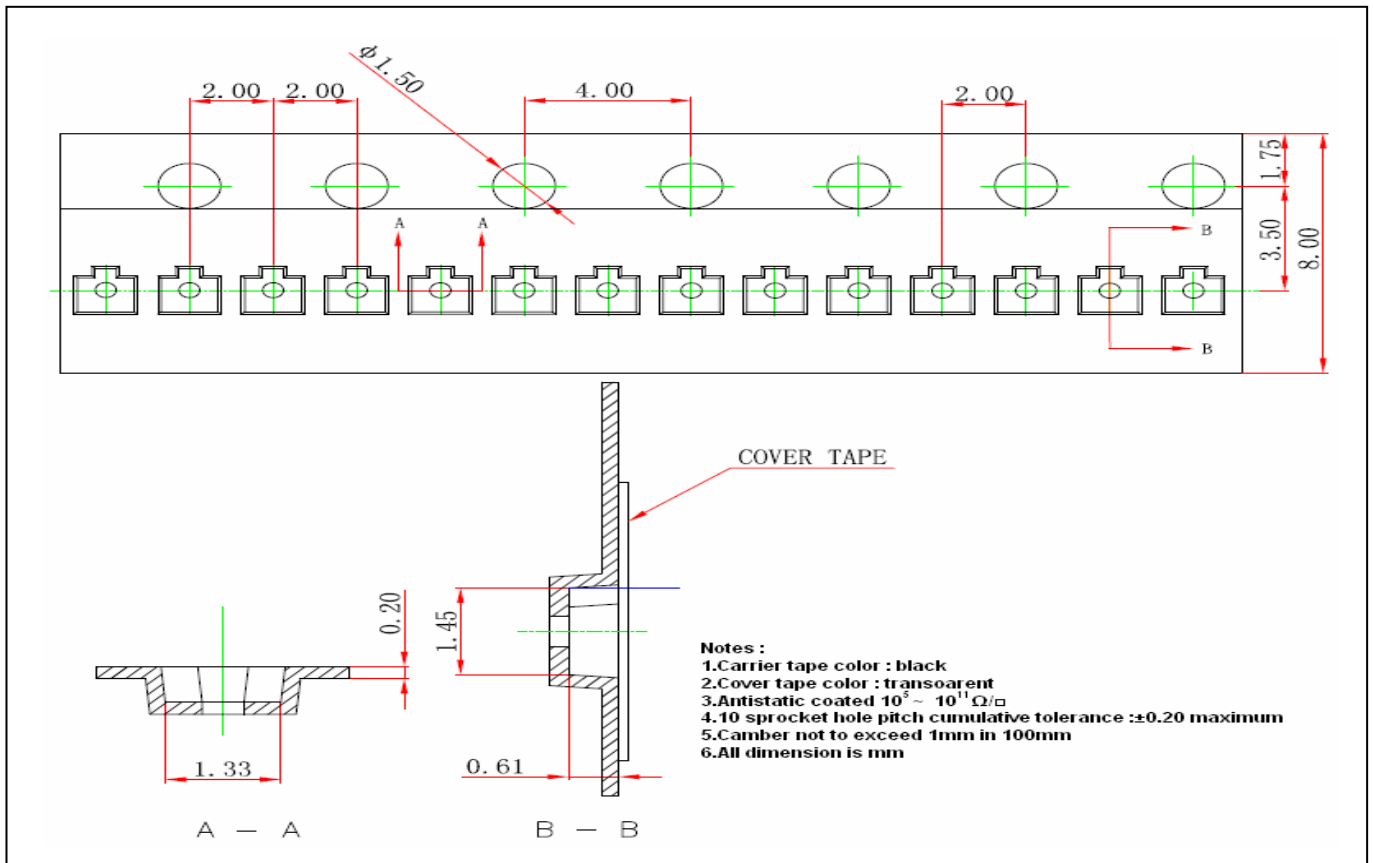
Power Derating Curve



**Reel Dimension**



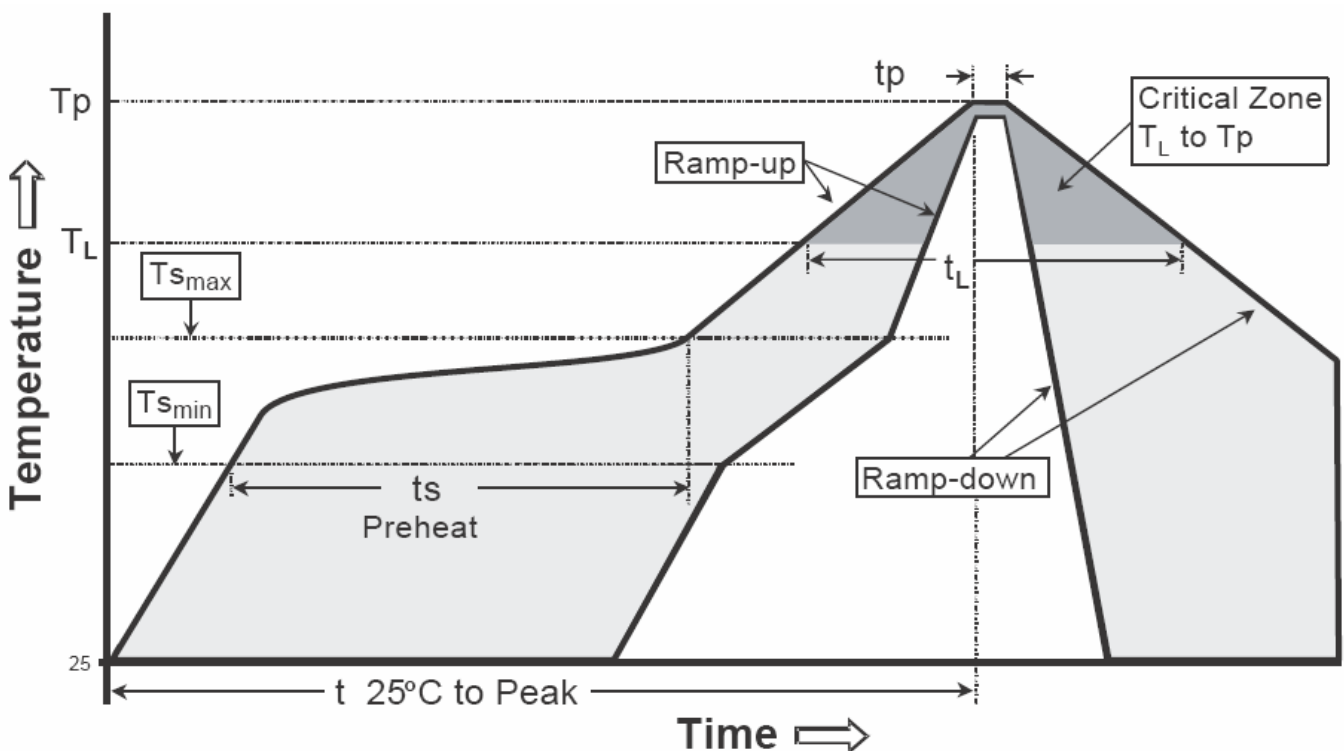
**Carrier Tape Dimension**



**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

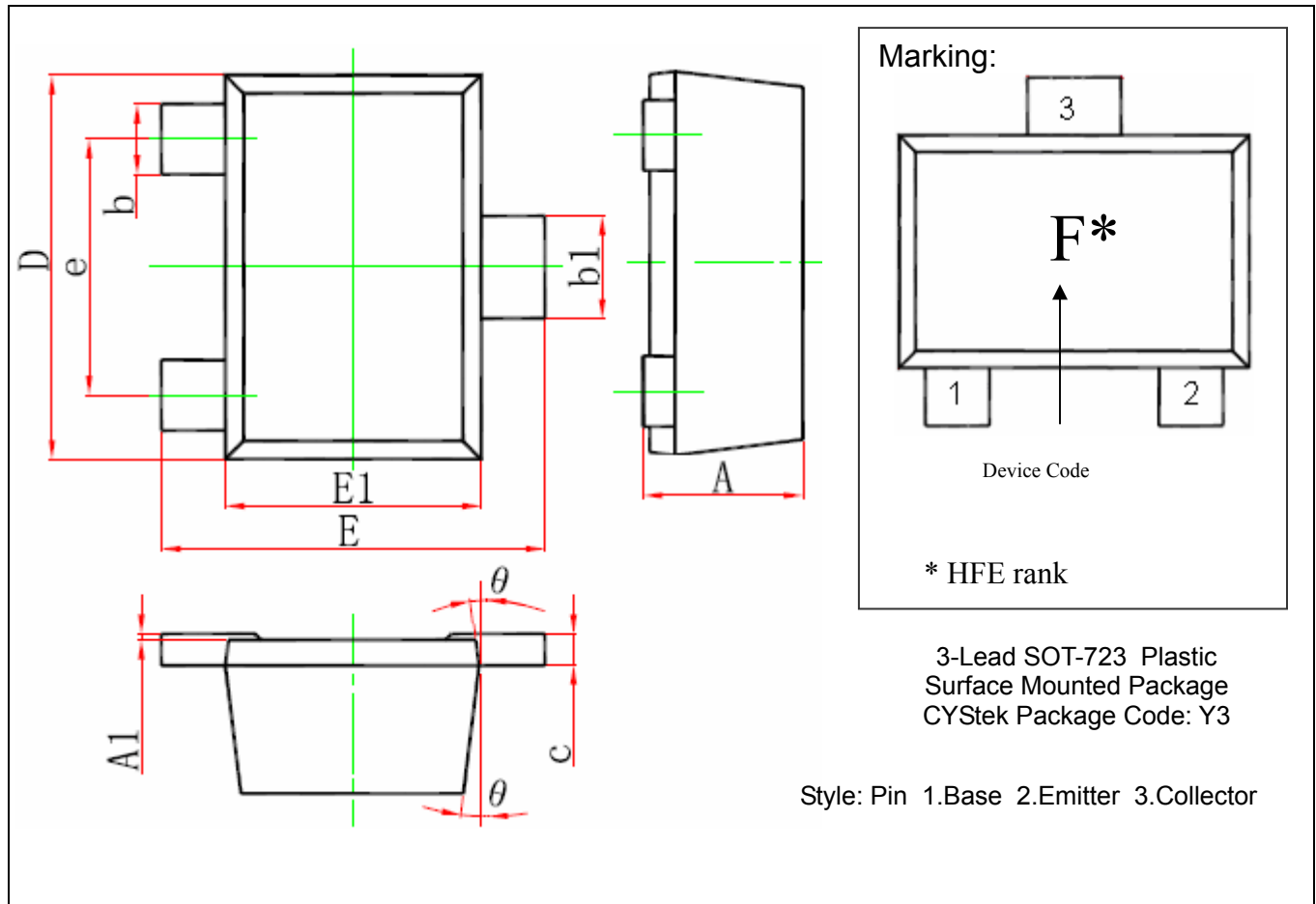
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (Tl)	183°C	217°C
- Time (tl)	60-150 seconds	60-150 seconds
Peak Temperature(Tp)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**SOT-723 Dimension**



\*Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.000	0.500	0.000	0.020	D	1.150	1.250	0.045	0.049
A1	0.000	0.050	0.000	0.002	E	1.150	1.250	0.045	0.049
b	0.170	0.270	0.007	0.011	E1	0.750	0.850	0.030	0.033
b1	0.270	0.370	0.011	0.015	e	0.800*		0.031*	
c	0.000	0.150	0.000	0.006	$\theta$	7° REF		7° REF	

**Notes:** 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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